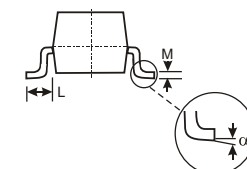
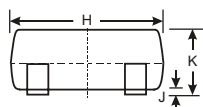
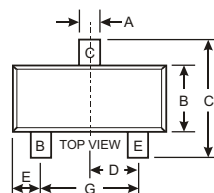


### Features

- High current capacity in compact package.
- NPN complement:MMBTSD1781
- Pb-Free Package is available.

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	-40	V
Collector Emitter Voltage	$V_{CEO}$	-25	V
Emitter Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-800	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	$0^\circ$	$8^\circ$
All Dimensions in mm		

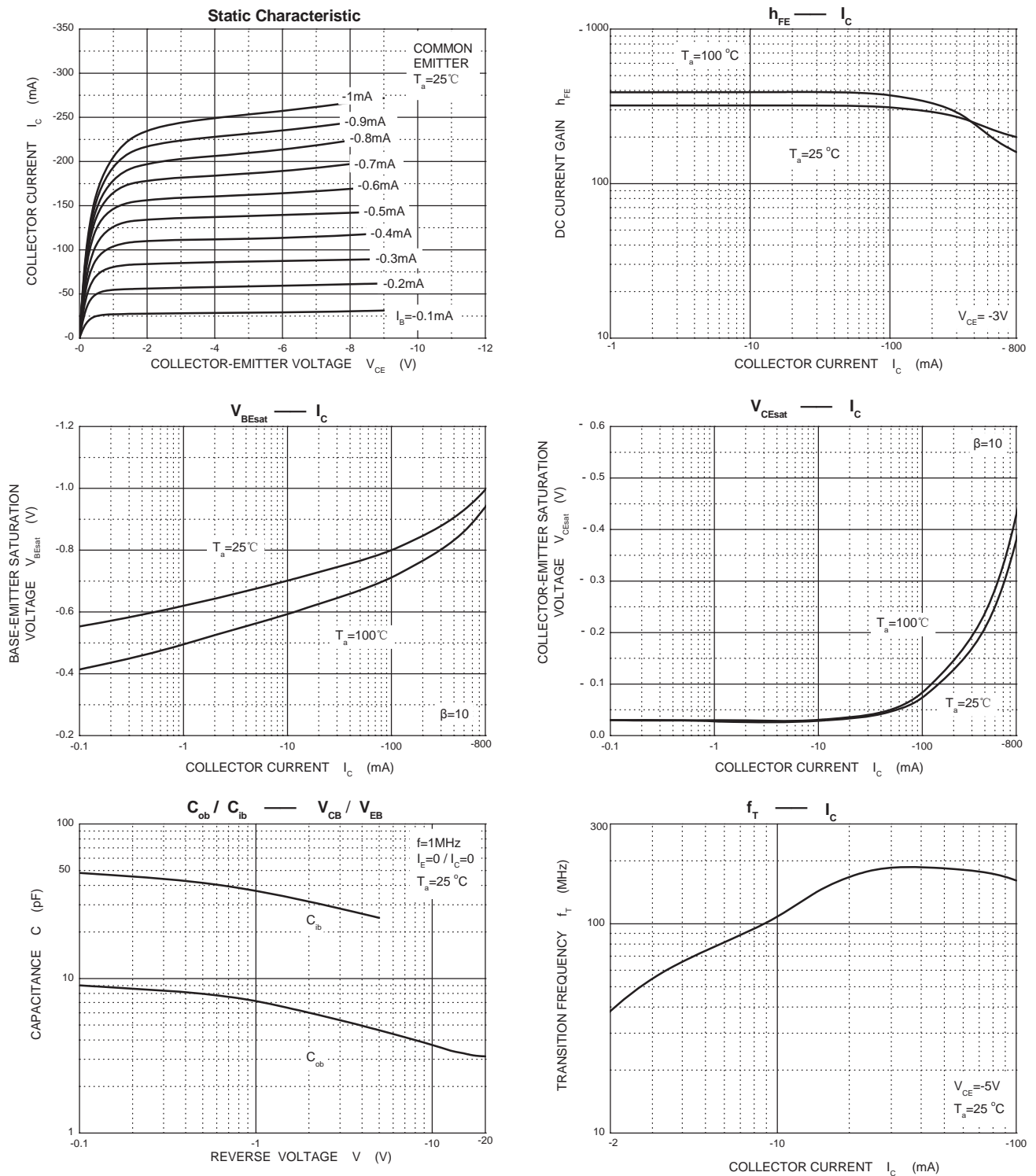
### Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	est conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20\text{V}, I_E = 0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -3\text{V}, I_C = -100\text{mA}$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.5	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$	50	20		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		12	30	pF

### CLASSIFICATION OF $h_{FE}$

Rank	Q	R
Range	120-270	180-390
Marking	AHQ	AHR

### TYPICAL TRANSIENT CHARACTERISTICS



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## IMPORTANT NOTICE

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